

### **AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application:

#### **Listing of Claims**

Claims 1-9 (cancelled).

Claim 10 (Currently Amended): A sound detecting mechanism comprising a pair of electrodes forming a capacitor on a substrate in which one of the electrodes is a back electrode forming perforations therein corresponding to acoustic holes and the other of the electrodes is a diaphragm,

wherein a multilayered assembly is mounted on the substrate, the multilayered assembly formed of the diaphragm, a sacrificial layer and the back electrode superposed in series by vapor deposition technique; ~~is mounted on the substrate while the back electrode is mounted in a position opposed to the diaphragm across a void to be supported by the substrate;~~

the sacrificial layer is etched relative to the multilayered assembly formed of the diaphragm, the sacrificial layer and the back electrode, thereby defining a void area between the diaphragm and the back electrode, with the sacrificial layer remaining at outer peripheral portions of the void area; and

the back electrode being formed by polycrystal silicon of 5 $\mu$ m to 20 $\mu$ m in thickness.

Claim 11 (Currently Amended): The sound detecting mechanism of claim 10, wherein the substrate comprises a support substrate having a monocrystal silicon substrate acting as the base thereof, and a silicon substrate of (100) orientation is used as the monocrystal silicon substrate.

Claim 12 (Previously Presented): The sound detecting mechanism of claim 10, wherein an impurity diffusion treatment is executed on the diaphragm.

Claim 13 (Currently Amended): The sound detecting mechanism of claim 10, wherein the substrate comprises a support substrate having a monocrystal silicon substrate acting as the base thereof, and the support substrate consists of ~~an SOI~~ a single crystal silicon on insulator (SOI) wafer.

Claim 14 (Currently Amended): The sound detecting mechanism of claim 13, wherein the ~~SOI~~ single crystal silicon on insulator (SOI) wafer has an active layer used as the diaphragm.

Claim 15 (Previously Presented): The sound detecting mechanism of claim 13, wherein the diaphragm is formed of monocrystal silicon of  $0.5\mu\text{m}$  to  $5\mu\text{m}$  in thickness.

Claim 16 (Currently Amended): The sound detecting mechanism of claim 10, wherein the substrate consists of ~~an SOI~~ a single crystal silicon on insulator (SOI) structure wafer including a silicon oxide film or a silicon nitride film formed on a monocrystal silicon substrate and a polycrystal silicon film formed on the silicon oxide film or the silicon nitride film.

Claim 17 (Currently Amended): The sound detecting mechanism of claim 16, wherein the polycrystal silicon film formed on the ~~SOI~~ single crystal silicon on insulator (SOI) structure wafer is used as the diaphragm.

Claim 18 (Previously Presented): The sound detecting mechanism of claim 16, wherein the diaphragm is formed of polycrystal silicon of  $0.5\mu\text{m}$  to  $5\mu\text{m}$  in thickness.